

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for processing an organosiloxane film, the method comprising:

loading a target substrate with a coating film formed thereon into a reaction chamber, the coating film comprising a polysiloxane base solution having an organic functional group; and

performing a heat process on the target substrate within the reaction chamber to bake the coating film, wherein the heat process comprises:

a temperature setting step of setting an interior of the reaction chamber at a process temperature by heating, and

a supplying step of supplying a baking gas into the reaction chamber set at the process temperature, while activating the baking gas by a gas activation section disposed outside the reaction chamber, the gas activation section activating the baking gas by bringing the baking gas into contact with a catalyst while supplying the baking gas with heat energy, wherein:

the baking gas is selected from the group consisting of ammonia gas and  
dinitrogen oxide gas, nitrogen oxide gas, hydrogen gas, argon gas, and nitrogen gas,  
and

the catalyst is ~~selected from the group consisting of tungsten,~~ and  
the gas activation section is configured to heat the baking gas to a temperature  
of from 700 to 1,000°C ~~titanium oxide.~~

Claim 2 (Original): The method according to claim 1, wherein the process temperature ranges from 250 to 400°C.

Claims 3-6 (Canceled).

Claim 7 (Currently Amended): An apparatus for processing an organosiloxane film, by performing a heat process on a target substrate with a coating film formed thereon to bake the coating film, the coating film comprising a polysiloxane base solution having an organic functional group, the apparatus comprising:

a reaction chamber configured to accommodate the target substrate;

a temperature adjusting section configured to adjust temperature inside the reaction chamber;

a gas supply section configured to supply a baking gas into the reaction chamber, the baking gas being selected from the group consisting of ammonia gas[,], and dinitrogen oxide gas, ~~nitrogen oxide gas, hydrogen gas, argon gas, and nitrogen gas;~~

a gas activation section disposed outside the reaction chamber and configured to activate the baking gas, the gas activation section being configured to activate the baking gas by bringing the baking gas into contact with a catalyst while supplying the baking gas with heat energy, the catalyst being tungsten, and the gas activation section being configured to heat the baking gas to a temperature of from 700 to 1000°C; selected from the group consisting of tungsten and titanium oxide;

an exhaust section configured to exhaust gas inside the reaction chamber; and

a control section configured to control the temperature adjusting section to perform said adjust step, control the gas supply section to perform said supply step, control the gas activation section to perform said activate step, and control the exhaust section to perform said exhaust step.

Claims 8-11 (Canceled).

Claim 12 (Previously Presented): The apparatus according to claim 7, wherein the control section is further configured to execute a heat process comprising:

a temperature setting step of setting an interior of the reaction chamber at a process temperature by heating, and

a supplying step of supplying the baking gas into the reaction chamber set at the process temperature, while activating the baking gas by the gas activation section disposed outside the reaction chamber.

Claim 13 (Original): The apparatus according to claim 7, wherein the process temperature ranges from 250 to 400°C.

Claims 14-16 (Canceled)

Claim 17 (Previously Presented): The method according to claim 1, wherein the reaction chamber is configured to accommodate a plurality of target substrates at intervals in a vertical direction, said loading comprising loading the plurality of target substrates.

Claims 18-20 (Canceled).

Claim 21 (Previously Presented): The apparatus according to claim 7, wherein the reaction chamber is configured to accommodate a plurality of target substrates at intervals in a vertical direction.